

Marked-Up Version to Show Changes Made

In the Claims

Please amend claims 1-5 as follows.

1. (Thrice Amended) A surface acoustic wave device comprising a piezoelectric substrate, a first interdigital transducer and a second interdigital transducer formed on a surface of the piezoelectric substrate so that the first and second interdigital transducers are opposed to each other,

wherein the piezoelectric substrate includes, in the surface between the first and second interdigital transducers, a region having a lower resistance than a resistance of an inner portion of the piezoelectric substrate [a doping region that is doped with a substance in at least one form selected from the group consisting of atoms, molecules and clusters in a surface between the first and second interdigital transducers].

2. (Amended) The surface acoustic wave device according to claim 1, wherein a depth of the [doping] region is not more than 50 nm.
3. (Amended) The surface acoustic wave device according to claim 1, wherein the [doping] region has a lower resistance than that of an inner portion of the substrate.
4. (Twice Amended) The surface acoustic wave device according to claim 3, wherein a sheet resistance of the [doping] region ranges from $10^8 \Omega/\text{square}$ to $10^{15} \Omega/\text{square}$.
5. (Twice Amended) The surface acoustic wave device according to claim 23 [1], wherein the substance is at least one selected from the group consisting of a reducing gas, silane, nitrogen, oxygen, argon, silicon, arsenic, boron, phosphorus, tin, indium, chromium, tantalum, molybdenum, germanium, and nickel.

Please add new claim 23 as follows.

23. (New) The surface acoustic wave device according to claim 1, wherein a substance in at least one form selected from the group consisting of atoms, molecules, clusters, ions and radicals is added to the substrate in the region.